Abstracts

Parameter-Extraction Method for Heterojunction Bipolar Transistors

S.A. Maas and D. Tait. "Parameter-Extraction Method for Heterojunction Bipolar Transistors." 1992 Microwave and Guided Wave Letters 2.12 (Dec. 1992 [MGWL]): 502-504.

A method for determining the equivalent-circuit element values of a small-signal heterojunction bipolar transistor (HBT) is described. Most important is the ability to separate the parasitic emitter resistance from the junction resistance. No use of "cold" measurements or test patterns is required. The method may also be applicable to homojunction bipolars.

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